

TMP11N50/TMPF11N50 TMP11N50G/TMPF11N50G

Features

- Low gate charge
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant
- Halogen free package
- JEDEC Qualification
- Fast reverse recovery

$$V_{DSS} = 550 \text{ V @ } T_{jmax}$$

$$I_D = 11 \text{ A}$$

$$R_{DS(ON)} = 0.67 \text{ (max) @ } V_{GS} = 10 \text{ V}$$

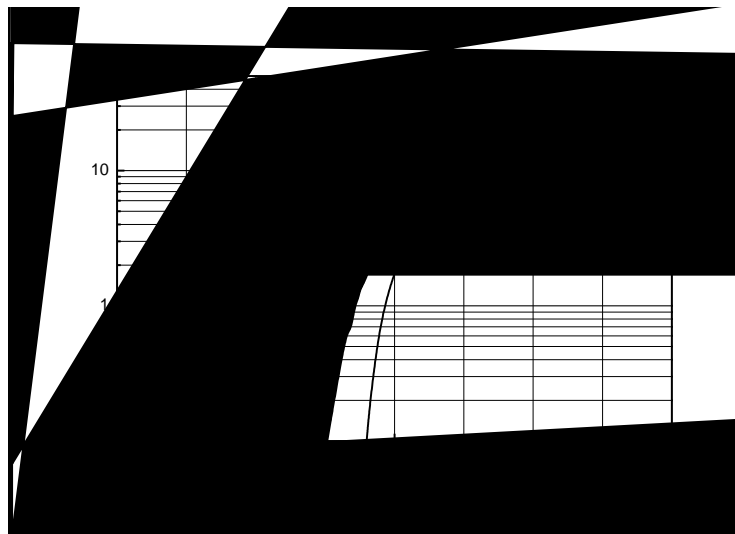
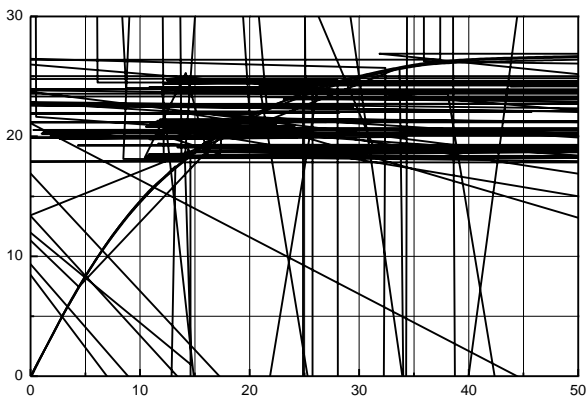
Absolute Maximum Ratings

Parameter	Symbol	TMP11N50(G)	TMPF11N50(G)	Unit
Drain-Source Voltage	V_{DSS}	500		V
Gate-Source Voltage	V_{GS}	±30		V
Continuous Drain Current	$T_C = 25 \text{ }^\circ\text{C}$	11	11 *	A
	$T_C = 100 \text{ }^\circ\text{C}$	6	6 *	A
Pulsed Drain Current (Note 1)	I_{DM}	44	44*	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	544		mJ
Repetitive Avalanche Current (Note 1)	I_{AR}	11		A
Repetitive Avalanche Energy (Note 1)	E_{AR}	15.8		mJ
Power Dissipation	$T_C = 25 \text{ }^\circ\text{C}$	158	51.4	W
	Derate above 25 °C	1.26	0.41	W/°C
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5		V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150		°C
Maximum lead temperature for soldering purposes,	T_L	300		°C

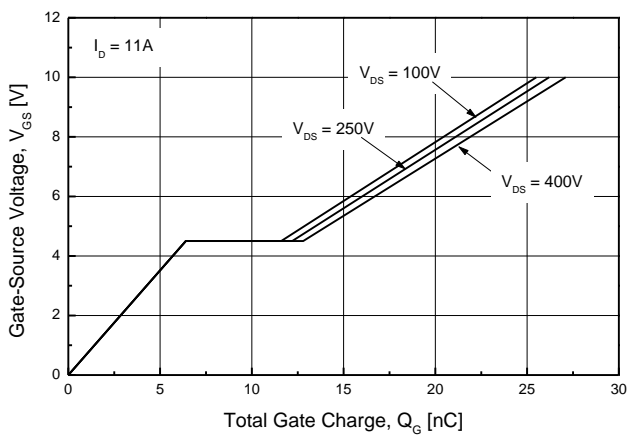
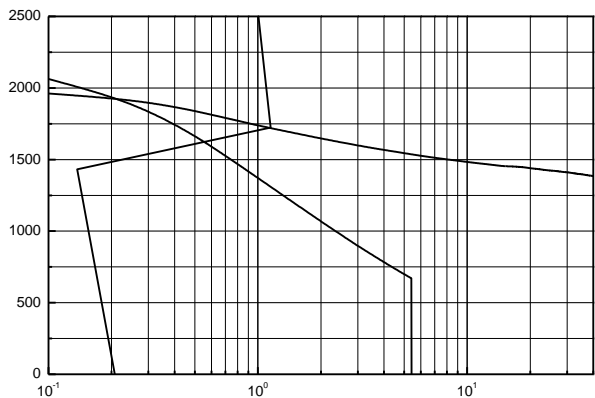
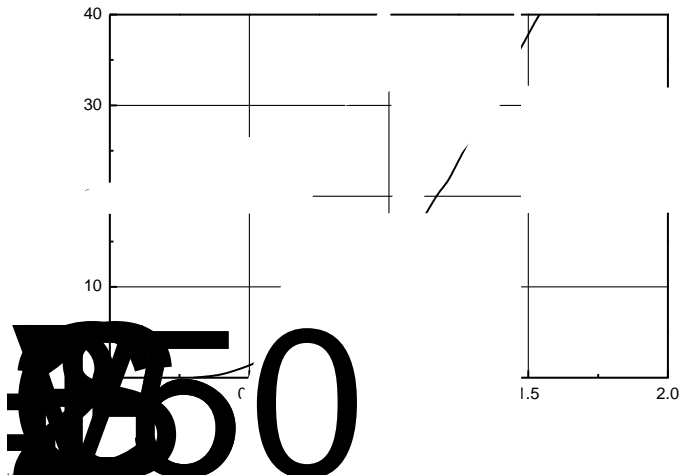
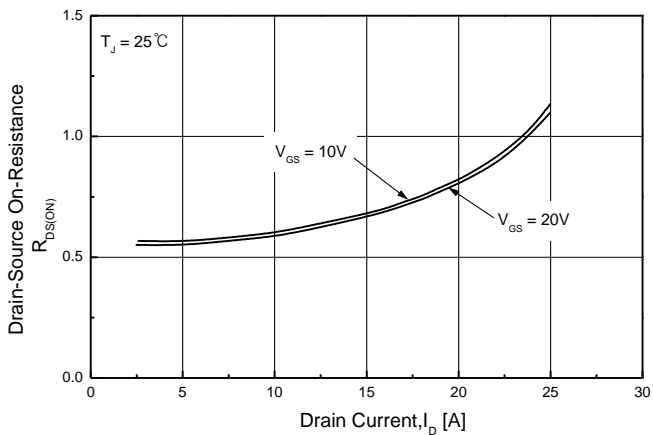
Thermal Characteristics

Parameter	Symbol			

TMP11N50/TMPF11N50 TMP11N50G/TMPF11N50G

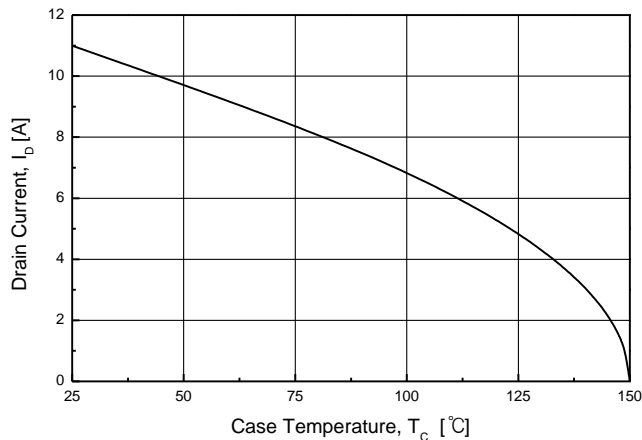
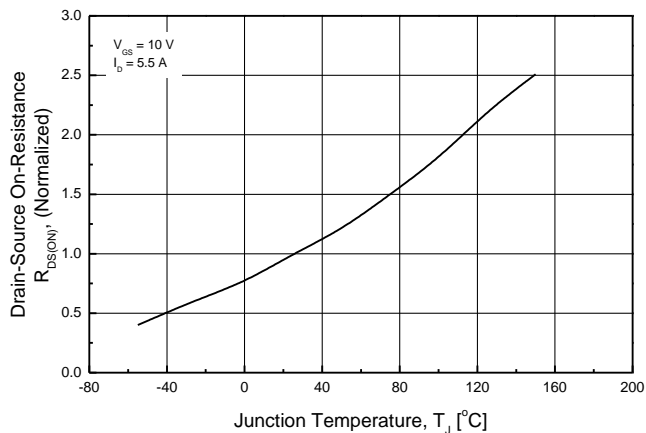
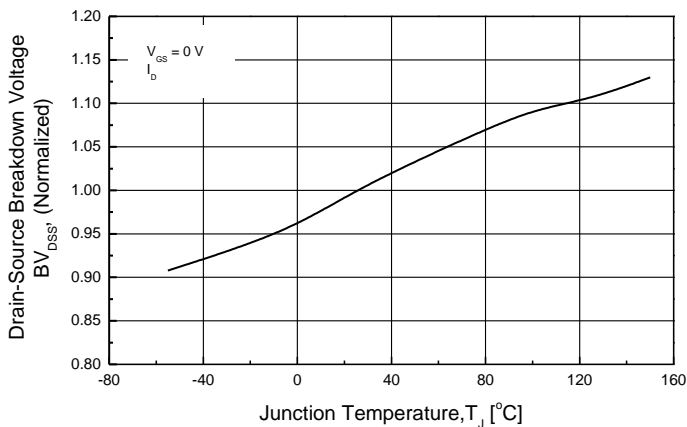


Drain Current, I_D

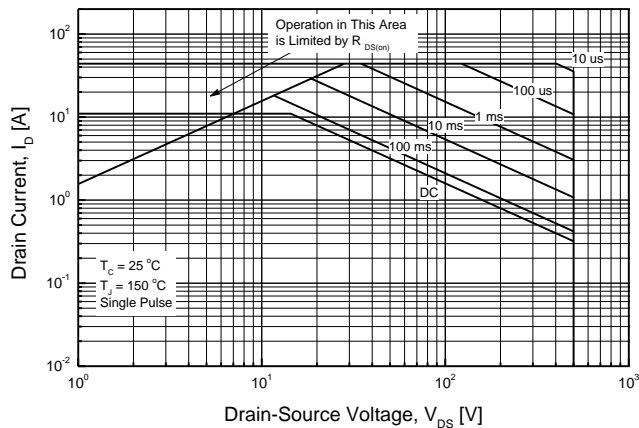


TMP11N50/TMPF11N50

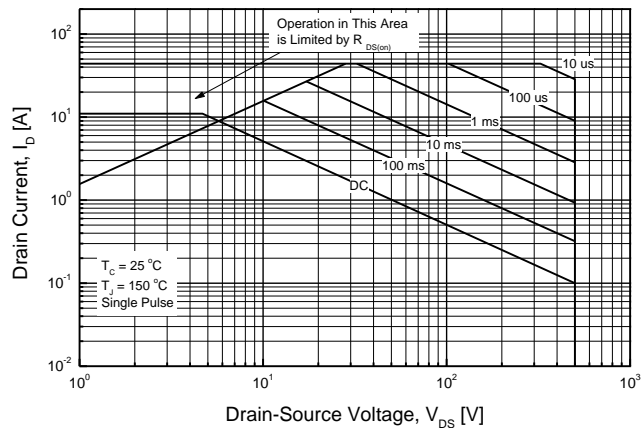
TMP11N50G/TMPF11N50G



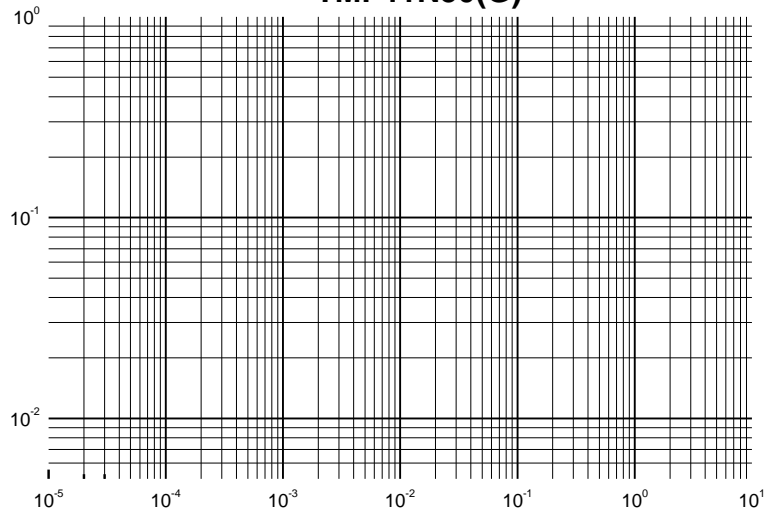
TMP11N50(G)



TMPF11N50(G)



TMP11N50(G)



TMPF11N50(G)

